

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection up to 1 kV
- Ultra thin package profile with 0.37 mm height

1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	-230	mA
Static charac	cteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$		-	4.5	7.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	1	D
3	D	drain	Transparent top view SOT883B (DFN1006B-3)	G S 017aaa259

3. Ordering information

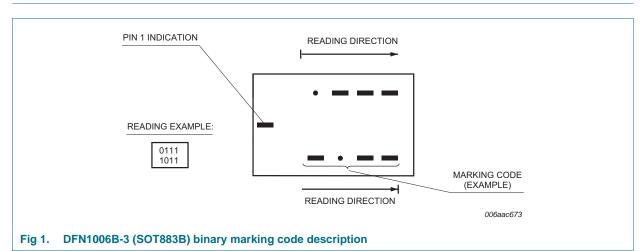
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BSS84AKMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.37 mm	SOT883B			

4. Marking

Table 4. Marking codes

Type number	Marking code
BSS84AKMB	0000 0010



BSS84AKMI

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	<u>[1]</u>	-	-230	mΑ
		V _{GS} = -10 V; T _{amb} = 100 °C	<u>[1]</u>	-	-150	mΑ
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			<u>[1]</u>	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-230	mΑ
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	1000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

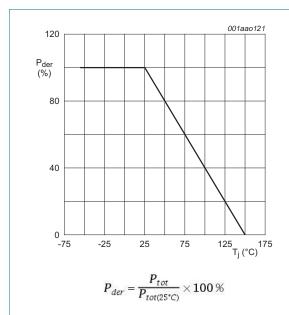


Fig 2. Normalized total power dissipation as a function of junction temperature

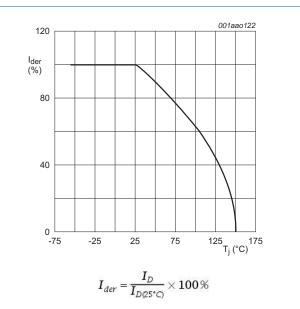
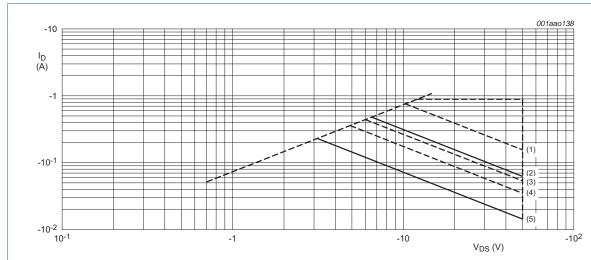


Fig 3. Normalized continuous drain current as a function of junction temperature

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I_{DM} is single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	305	350	K/W
	from junction to ambient		[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

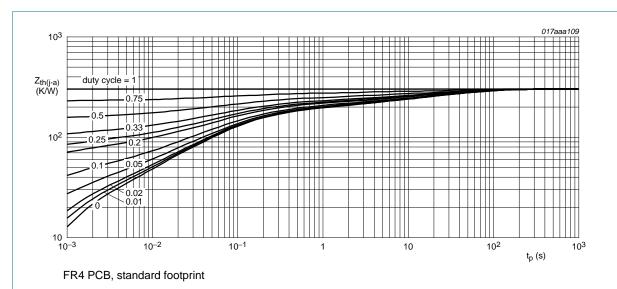


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

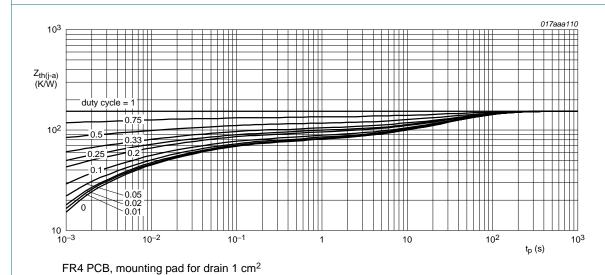


Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		V _{DS} = -50 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-2	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	4.5	7.5	Ω
	resistance	V_{GS} = -10 V; I_{D} = -100 mA; T_{j} = 150 °C	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	5.7	8.5	Ω
9fs	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge	V_{DS} = -10 V; I_{D} = -200 mA; V_{GS} = -5 V; T_{j} = 25 °C	-	0.09	-	nC
C _{iss}	input capacitance	$V_{DS} = -25 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -30 V; R_L = 250 Ω ; V_{GS} = -10 V;	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.48	-0.85	-1.2	V

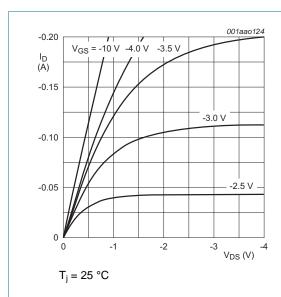
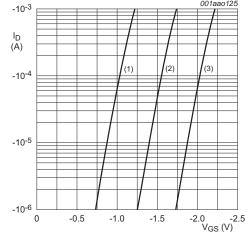


Fig 7. Output characteristics; drain current as a function of drain-source voltage; typical values



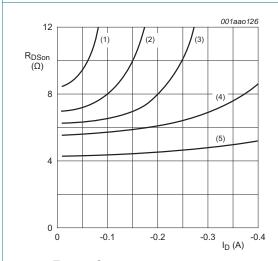
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 8. Subthreshold drain current as a function of gate-source voltage



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -3.0 \text{ V}$

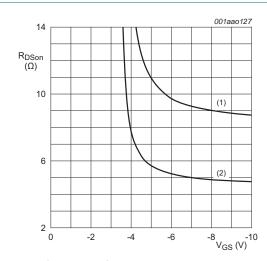
(2) $V_{GS} = -3.5 \text{ V}$

(3) $V_{GS} = -4.0 \text{ V}$

(4) $V_{GS} = -5.0 \text{ V}$

 $(5) V_{GS} = -10.0 V$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = -200 \text{ mA}$

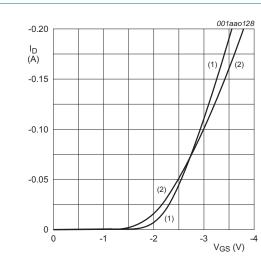
(1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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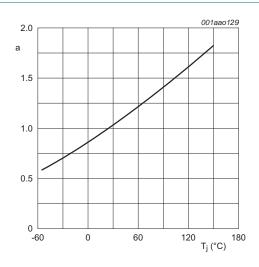


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

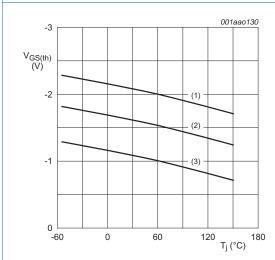
(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

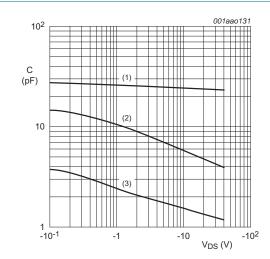
Fig 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 13. Gate-source threshold voltage as a function of junction temperature

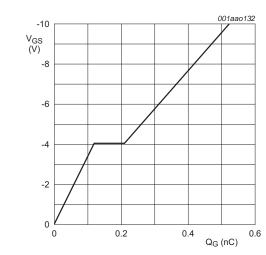


 $f = 1 \text{ MHz}, V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = -0.2 A; V_{DS} = -25 V; T_{amb} = 25 °C

Fig 15. Gate-source voltage as a function of gate charge; typical values

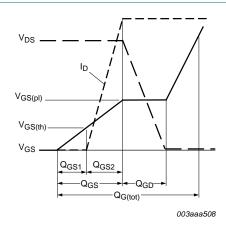
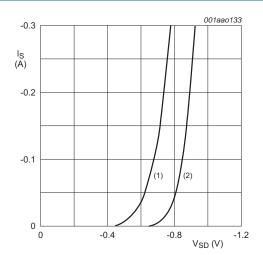


Fig 16. Gate charge waveform definitions



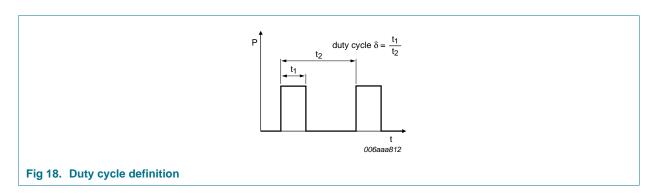
 $V_{GS} = 0 V$

(1) $T_j = 150 \, ^{\circ}\text{C}$

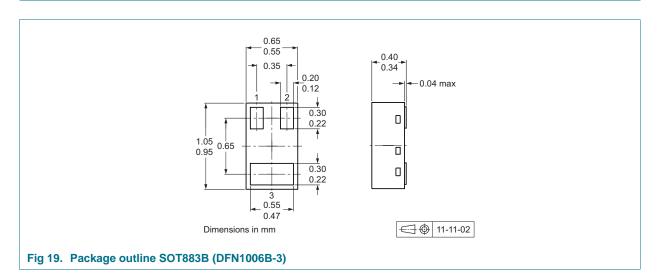
(2) $T_i = 25 \, ^{\circ}C$

Fig 17. Source current as a function of source-drain voltage; typical values

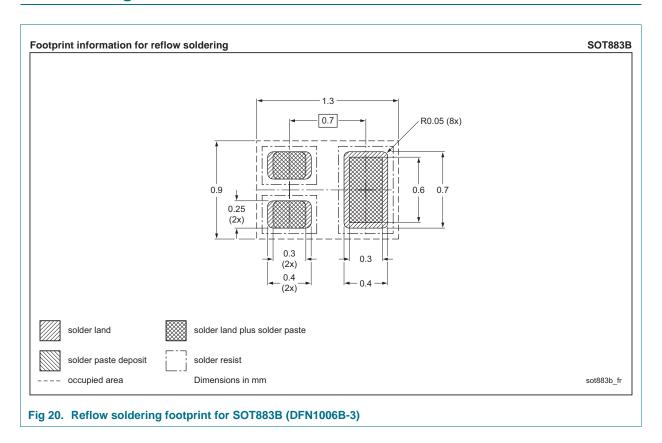
8. Test information



9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKMB v.1	20120606	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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